

Philips

Diode PBYR340CTD

Datasheet

Schottky Dual Diode

PBYR340CTD

40V / 3A

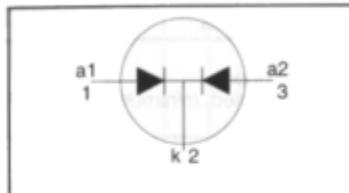
DATASHEET

OEM – Philips

Source: Philips Databook 1999

**Rectifier diodes
Schottky barrier**
PBYR345CTD series
FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

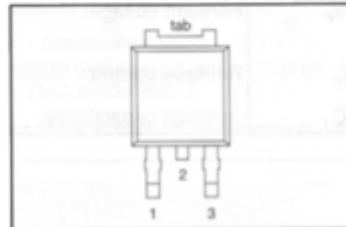
SYMBOL**QUICK REFERENCE DATA** $V_R = 40 \text{ V} / 45 \text{ V}$ $I_{O(AV)} = 3 \text{ A}$ $V_F \leq 0.57 \text{ V}$ **GENERAL DESCRIPTION**

Dual schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR345CTD series is supplied in the SOT428 surface mounting package.

PINNING

PIN	DESCRIPTION
1	anode 1
2	cathode ¹
3	anode 2
tab	cathode

SOT428**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	Peak repetitive reverse voltage		-	40CTD 40	V
V_{RWM}	Working peak reverse voltage		-	40	V
V_R	Continuous reverse voltage	$T_{mb} \leq 115 \text{ }^\circ\text{C}$	-	40	V
$I_{O(AV)}$	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \leq 142 \text{ }^\circ\text{C}$	-	3	A
I_{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \leq 142 \text{ }^\circ\text{C}$	-	3	A
I_{FSM}	Non-repetitive peak forward current per diode	$t = 10 \text{ ms}$ $t = 8.3 \text{ ms}$ sinusoidal; $T_j = 125 \text{ }^\circ\text{C}$ prior to surge; with reapplied $V_{RRM(max)}$ pulse width and repetition rate limited by T_{jmax}	-	55 60	A
I_{IRM}	Peak repetitive reverse surge current per diode		-	1	A
T_j	Operating junction temperature		-	150	$^\circ\text{C}$
T_{sg}	Storage temperature		-65	175	$^\circ\text{C}$

¹ it is not possible to make connection to pin 2 of the SOT428 package

Rectifier diodes Schottky barrier	PBYR345CTD series
--------------------------------------	-------------------

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th,j-mb}$	Thermal resistance junction to mounting base	per diode both diodes	-	-	5	K/W
$R_{th,j-a}$	Thermal resistance junction to ambient	pcb mounted, minimum footprint, FR4 board	-	50	-	K/W

ELECTRICAL CHARACTERISTICSAll characteristics are per diode at $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	$I_F = 1.5 \text{ A}; T_j = 125^\circ\text{C}$ $I_F = 3 \text{ A}; T_j = 125^\circ\text{C}$ $I_F = 3 \text{ A}$	-	0.51	0.57	V
I_R	Reverse current	$V_R = V_{RWM}$ $V_R = V_{RWM}; T_j = 100^\circ\text{C}$	-	0.05	0.2	mA
C_d	Junction capacitance	$V_R = 5 \text{ V}; f = 1 \text{ MHz}, T_j = 25^\circ\text{C} \text{ to } 125^\circ\text{C}$	-	3.2	8	mA
			-	65	-	pF

Rectifier diodes
Schottky barrier

PBYR345CTD series
Schottky barrier

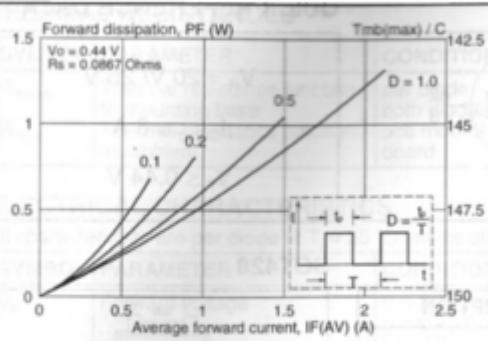


Fig.1. Maximum forward dissipation per diode
 $P_F = f(I_{F(AV)})$; square current waveform where
 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

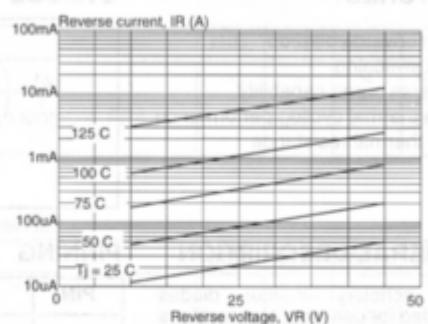


Fig.4. Typical reverse leakage current per diode;
 $I_R = f(V_R)$; parameter T_j

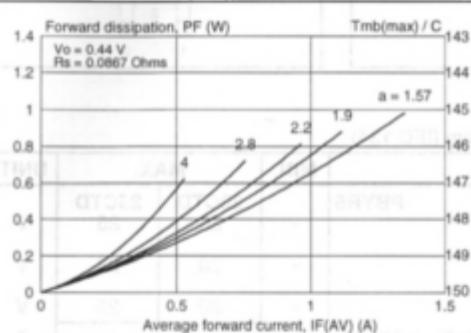


Fig.2. Maximum forward dissipation per diode
 $P_F = f(I_{F(AV)})$; sinusoidal current waveform where
 $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$.

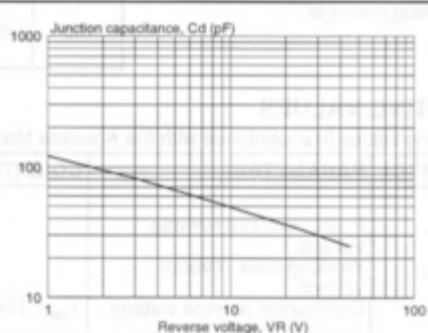


Fig.5. Typical junction capacitance per diode;
 $C_d = f(V_R)$; $f = 1 \text{ MHz}$; $T_j = 25^\circ C$ to $125^\circ C$.

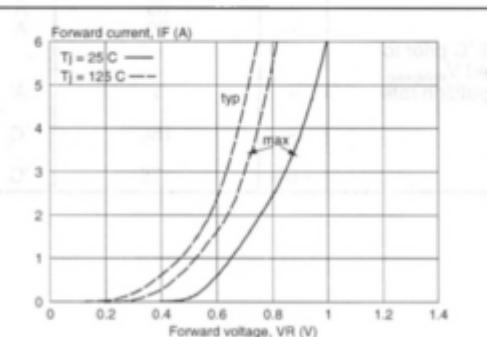


Fig.3. Typical and maximum forward characteristic per diode $I_F = f(V_F)$; parameter T_j .

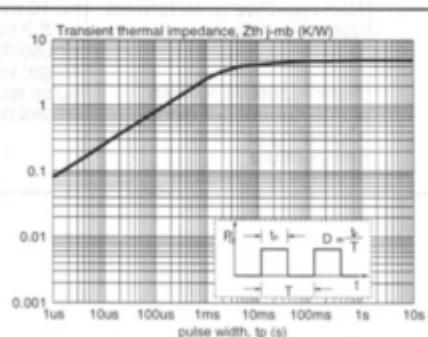


Fig.6. Transient thermal impedance per diode;
 $Z_{th-j\text{-mb}} = f(t_p)$.